

# Double Patterning Jumps the 200wph Hurdle: Coat/Develop Track Equipment

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SOKUDO Lithography Breakfast Forum  
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**SOKUDO DUO**

# “Photo” Double Patterning Resist Process Options

	Litho-Freeze chemical b/w 1 <sup>st</sup> & 2 <sup>nd</sup> Resist	Self-Freeze by 2 <sup>nd</sup> Resist Coat & Bake	UV Cure Freeze	Negative Tone Dev. Resist	Evaluation Partners per Technical Papers
JSR	😊	○	△	--	IMEC, Albany
TOK	--	😊	--	--	Nikon, IMEC
FujiFilm	--	--	--	😊	IMEC
Rohm & Haas	○	○	--	--	CEA-LETI
Shin-Etsu	--	○	△	--	AMD, Ushio, Sokudo/ AMAT

Possible with  
SOKUDO DUO

Complex Process  
on Track but  
Good Results !!!

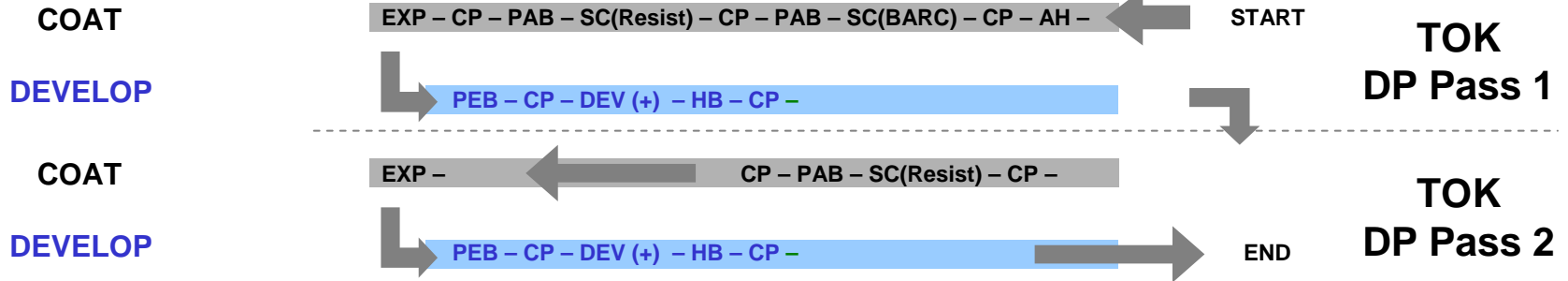
Preferred but  
Weak Results  
(will improve)

Needs More  
R&D Effort  
but Attractive  
if it can work!

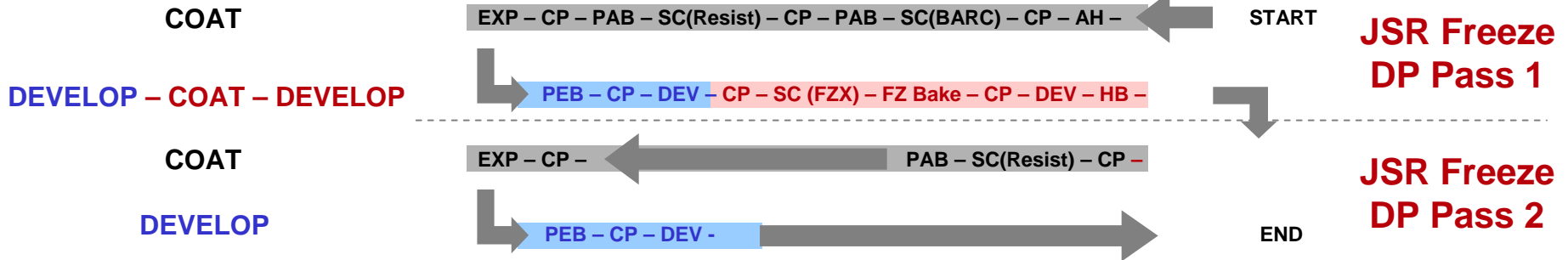
Potential for  
Niche Apps.  
(trench, CH)

# “Photo” Double Patterning Resist Process Example

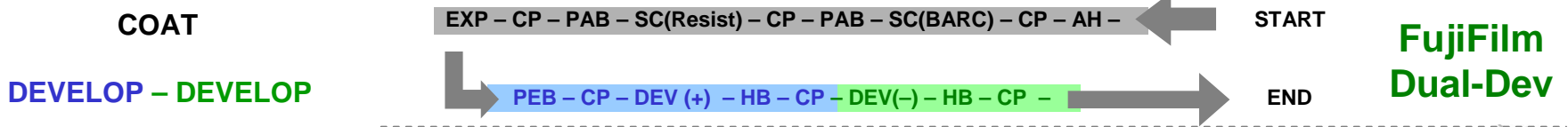
## TOK Freeze-Free



## JSR Freeze-Coat



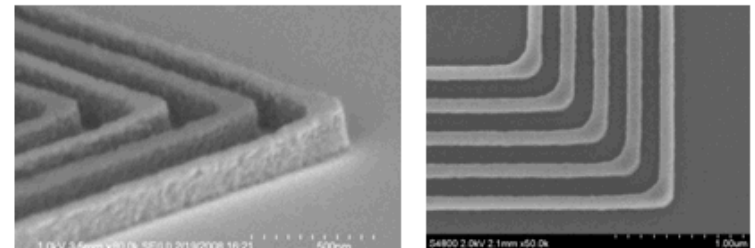
## FujiFilm Dual-Develop



## Myth: Semiconductor IC manufacturers only need one Double Patterning Solution that works for them

- **Reality: One Double Patterning Solution will not cover all IC process pattern scenarios, will need multiple “photo” Double Patterning solutions:**

- Dense lines (straight)
- Dense lines (elbow)
- Contact holes, dense / iso
- Trench patterns
- Etc.

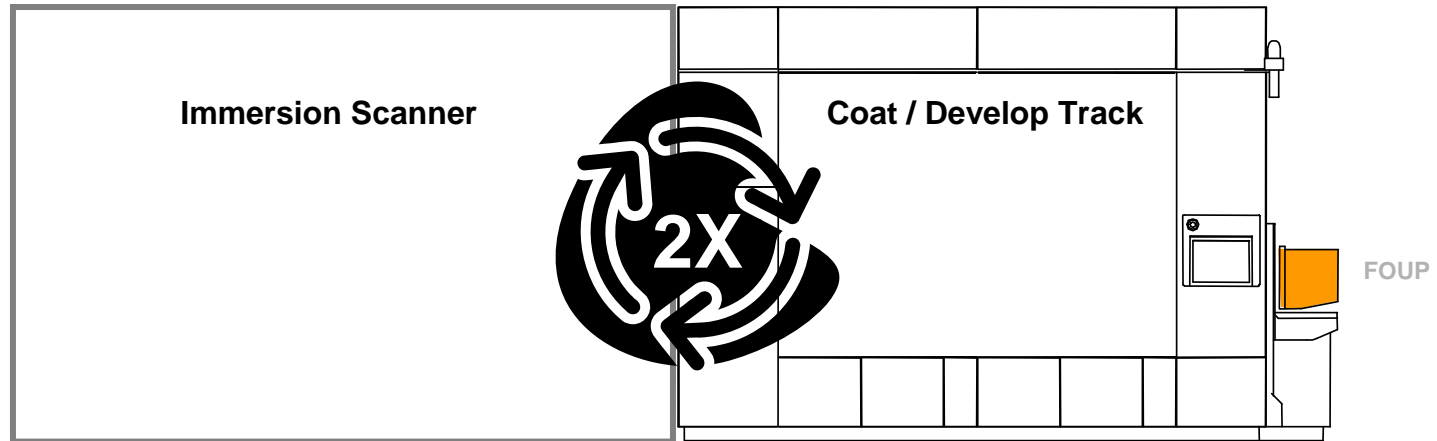


- **Therefore... Coat/Develop Track needs flexibility to run whatever “Double Patterning Solution” that fits the IC process pattern layer**

## >200wph Double Patterning Requirements for Coat/Develop Track

- **Flexibility to run whatever “Double Patterning Solution” that fits the IC process pattern layer**
  - Coat/develop track should not limit options of manufacturer
- **Maintain >200wph throughput even with extra process steps demanded by each Double Patterning solution**
  - Expandable to support adding coat, develop and bake units
  - Enable multi-pass flows (i.e. two-step develop in one flow)
- **Maintain continuous supply of wafers inside track:  
FOUP / Wafer Buffering**

# “Photo” Double Patterning = Two-Cycles Through Lithocell



## • Two-Cycle Wafer Flow Management Dilemma

- Semiconductor Fab Host reloads FOUP cassette for 2<sup>nd</sup> cycle or
- Track internally manages auto-start of second cycle/pattern and communicated to scanner via linked-litho network

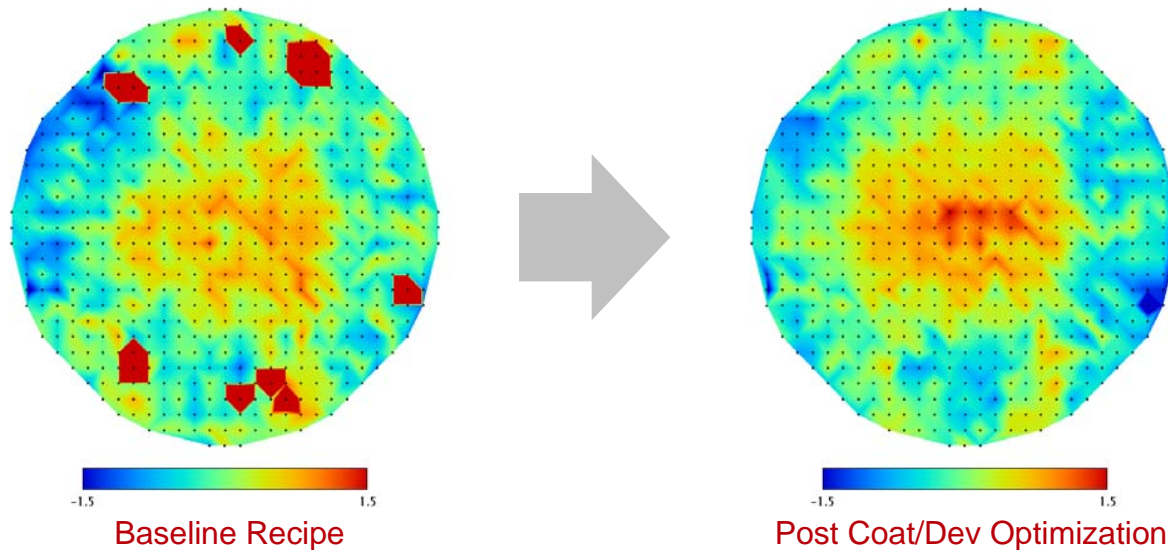
- **Solution:** Clear protocol with fab host and track/scanner on second cycle DP wafer reloading

# SOKUDO 22nm Double Patterning Process Development at IMEC





# JSR Freeze Coat – Develop Process Optimization

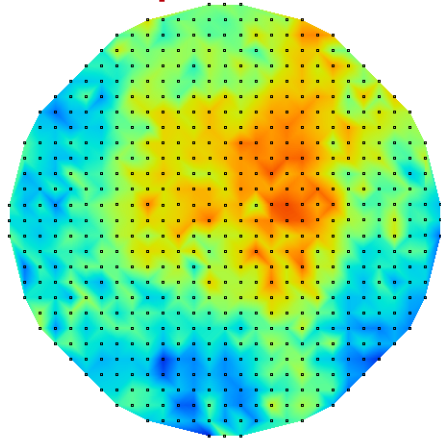


- **CDU & Defectivity was Unacceptable with Initial Baseline Process**
  - Freeze Material was Not Properly Removed due to Poor Wetting
- **Coat & Develop Optimization Complete: CDU ~1.5nm 3 $\sigma$** 
  - Defects from Remaining Freeze Material Resolved
- **Next... Evaluated cdTune<sup>tm</sup> at Freeze PAB to Optimize CDU**
  - Model Predicts ~1nm 3 $\sigma$



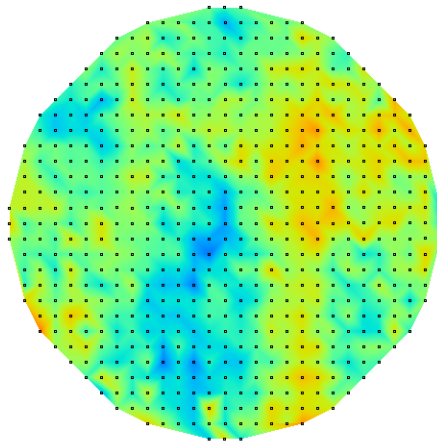
# Resist #1 CDU Tuning

POR Wafers  
Temp. Unif. PEB

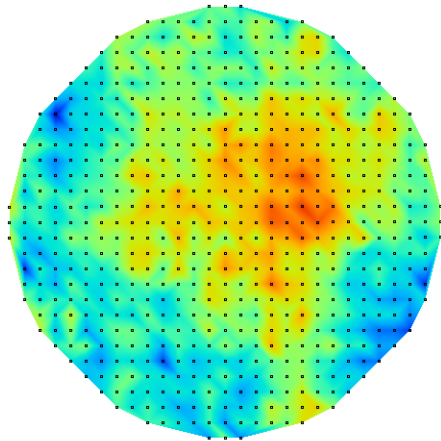


-1.2 1.2  
 $3\sigma=1.15\text{nm}$

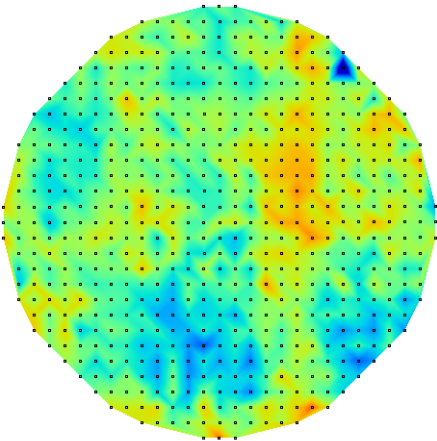
BHP  
cdTune



-1.2 1.2  
 $3\sigma=0.93\text{nm}$



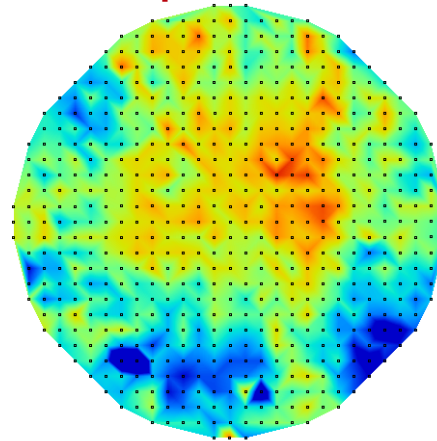
-1.2 1.2  
 $3\sigma=1.29\text{nm}$



-1.2 1.2  
 $3\sigma=0.86\text{nm}$

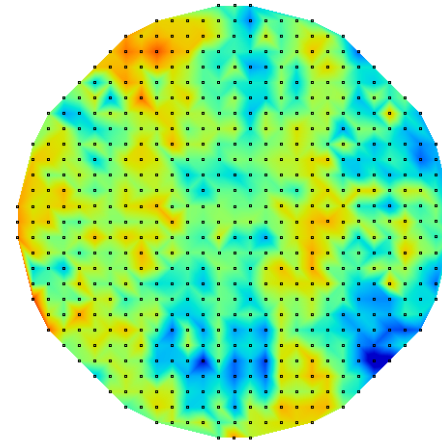
# Post-FZX CDU Tuning

POR Wafers  
Temp. Unif. PAB

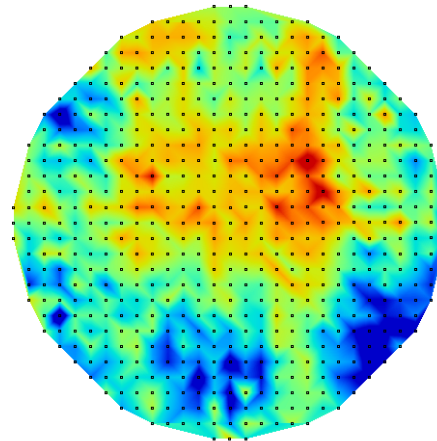


-1.2 1.2  
 $3\sigma=1.38\text{nm}$

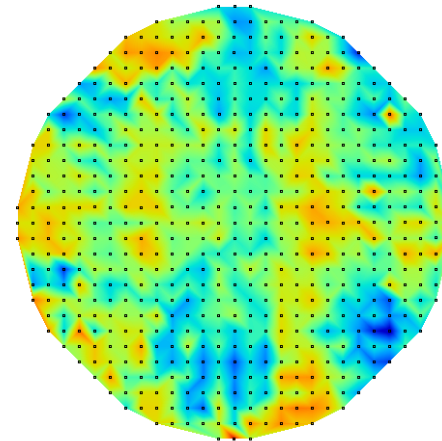
BHP  
cdTune



-1.2 1.2  
 $3\sigma=1.10\text{nm}$



-1.2 1.2  
 $3\sigma=1.56\text{nm}$

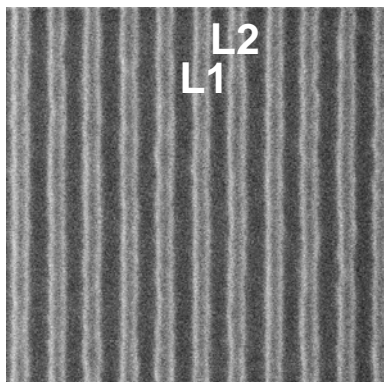


-1.2 1.2  
 $3\sigma=1.14\text{nm}$

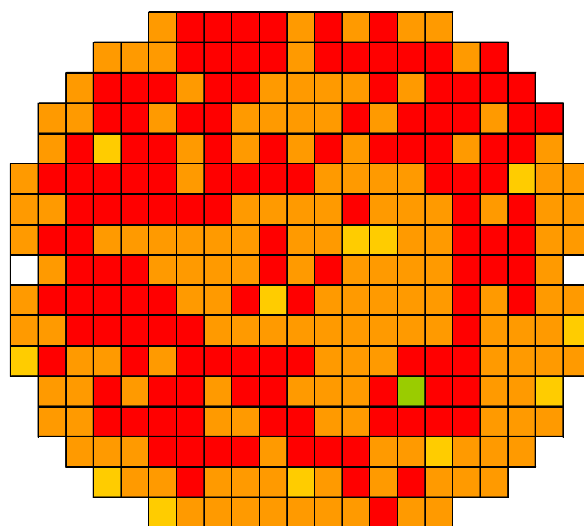
# TOK “Freeze Free” DP, 32nm HP CDU Results



Data courtesy  
of IMEC & TOK

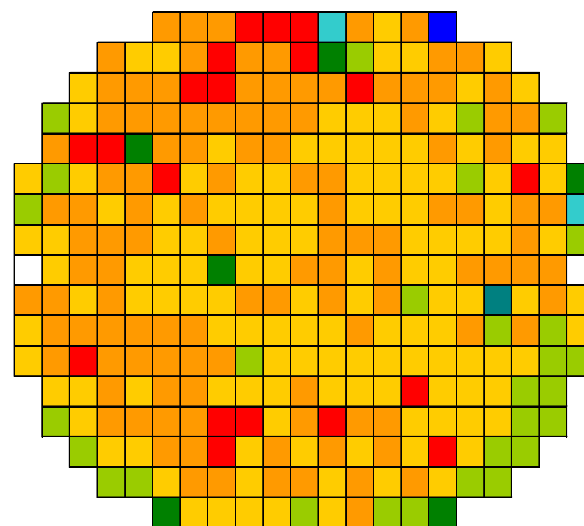


### L1 CDU



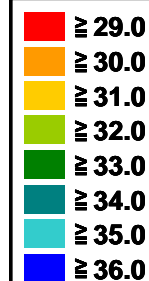
Ave. CD 30.1nm  
3 $\sigma$  1.45nm  
Ave. LWR 3.76nm

### L2 CDU



Ave. CD 31.2nm  
3 $\sigma$  2.74nm  
Ave. LWR 4.54nm

CD (nm)



- ◆ Target: 32nm DHP
- ◆ Film thickness was optimized to prevent pattern collapsing
- ◆ CDU indicated applicable value to further investigations

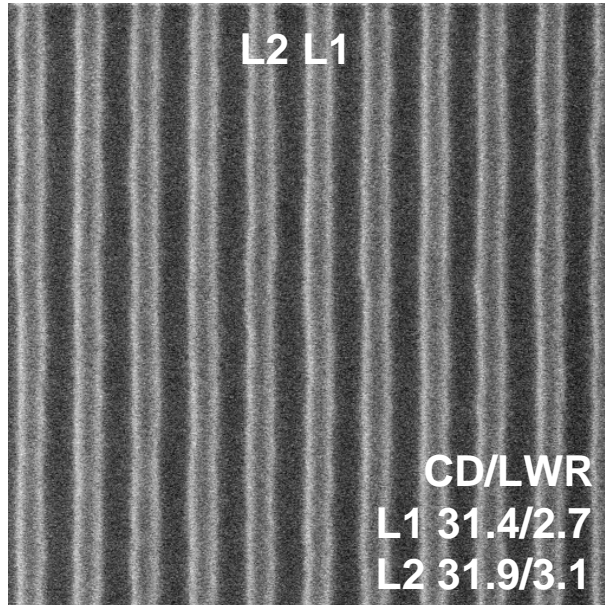




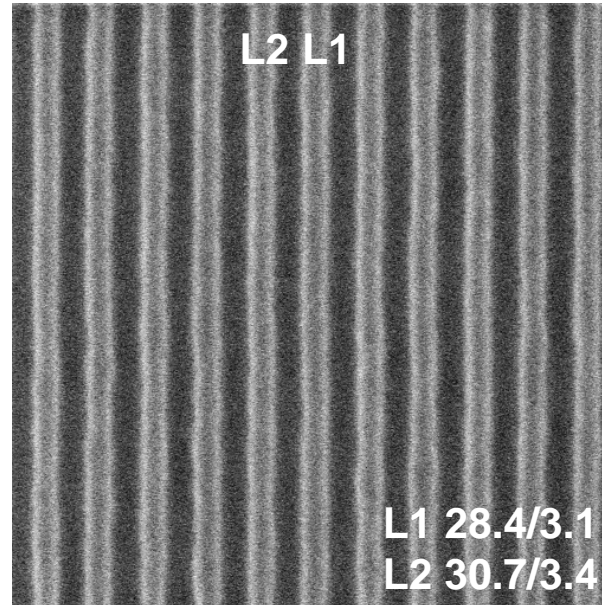
# TOK "Freeze Free" DP @ NA 1.0 dipole



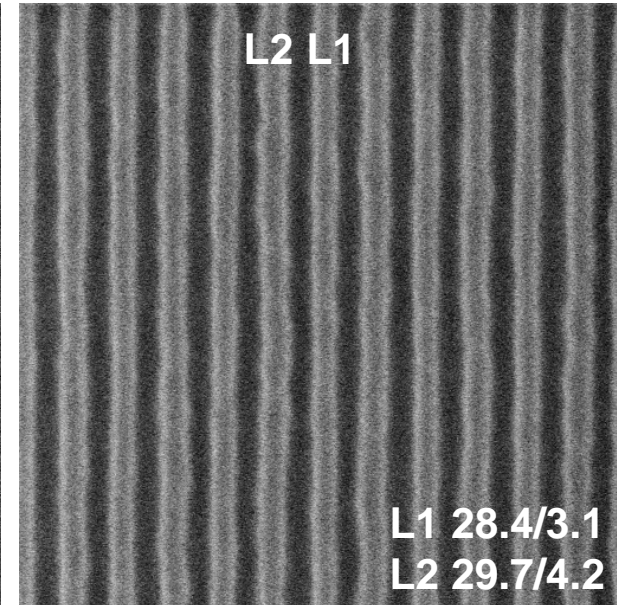
32nm DHP



30nm DHP



28nm DHP



- ◆ Target: 32nm DHP
- ◆ Film thickness was optimized to prevent pattern collapsing.  
→ Thinner setting both 1<sup>st</sup> level resist and 2<sup>nd</sup> level resist.
- ◆ 30 & 28nm HP patterns were obtained utilizing dipole illumination.

*Data courtesy of IMEC & TOK*



# Key Message: **SOKUDO DUO for Double Patterning**

- **SOKUDO DUO Immersion Track Qualifying @ 250wph**
- **SOKUDO DUO flexible to meet >200wph requirement for multiple Double Patterning Alternatives**
- **SOKUDO on the leading-edge of Double Patterning process know-how in collaboration with IMEC**



***SOKUDO DUO***

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